

Abstract of the Disclosure

The present invention is related to a method for fabricating a semiconductor device capable of preventing
5 occurrences of void and seam phenomena caused by a negative slope of an insulation layer or a bowing profile phenomenon in a cross-sectioned etch profile of a contact hole. To achieve this effect, the attack barrier layer or the capping layer is additionally deposited on the profile containing self-aligned
10 contact holes in order to prevent an undercut of the inter-layer insulation layer, which is a main cause of the seam generations. Also, the attack barrier layer has a function of preventing the inter-layer insulation layer from being attacked during the wet cleaning/etching process. Ultimately,
15 it is possible to improve device characteristics with the prevention of the seam generations.